QM4015S

P-Channel 40V Fast Switching MOSFET

General Description

The QM4015S is a high performance trench P-channel MOSFET which utilizes extremely high cell density to provide low Rdson and gate charge characteristics. It is ideally suited to support synchronous buck converter applications.

The QM4015S meets RoHS and Green Product requirements while supporting full function reliability.

Features

- ✓ Advanced high cell density Trench technology
- ✓ Super Low Gate Charge
- ✓ Excellent CdV/dt effect decline
- ✓ Green Device Available

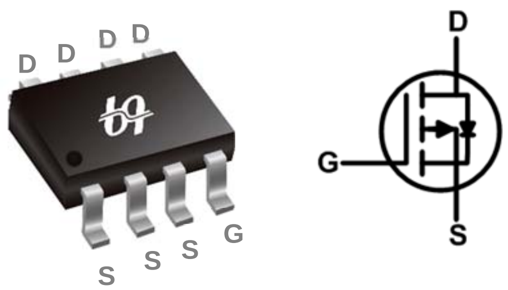
Product Summary

V_{DS}	$R_{DS(ON)}$ max (V_{GS}=-10V)	I_D (T_A=25 °C)
-40V	13mΩ	-8.7A

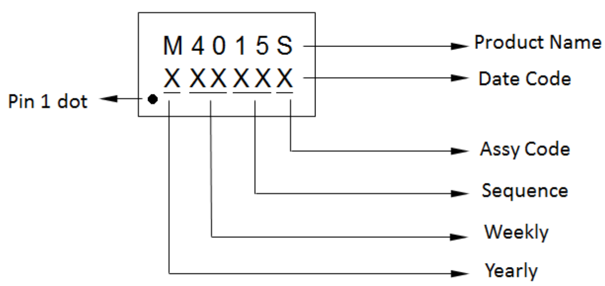
Applications

- ✓ High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- ✓ Networking DC-DC Power System
- ✓ Load Switch

Pin Configuration



Ordering Information

Order Number	Package Type	Top Marking
QM4015S	SOP8	

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Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25°C	Continuous Drain Current, V_{GS} @ -10V[1]	-8.7	A
I_D@T_A=70°C	Continuous Drain Current, V_{GS} @ -10V[1]	-7	A
I_{DM}	Pulsed Drain Current[2]	-18	A
EAS	Single Pulse Avalanche Energy[3]	262	mJ
I_{AS}	Avalanche Current	-54	A
P_D@T_A=25°C	Total Power Dissipation[4]	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	--	85	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	--	24	°C/W

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P-Channel Electrical Characteristics

P-Channel Electrical Characteristics: (T_J=25 ℃, unless otherwise noted)						
Symbol	**Parameter**	**Conditions**	**Min**	**Typ**	**Max**	**Unit**
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-40	--	--	V
$\triangle BV_{DSS}$ /$\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25°C , I_D=-1mA	--	-0.023	--	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-8A	--	10.5	13	mΩ
		V_{GS}=-4.5V , I_D=-6A	--	16	20	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	-1.6	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		--	4.74	--	mV/°C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-32V , V_{GS}=0V , T_J=25°C	--	--	-1	uA
		V_{DS}=-32V , V_{GS}=0V , T_J=55°C	--	--	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	--	--	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-8A	--	27	--	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	--	7	14	Ω
Q_g	Total Gate Charge	V_{DS}=-20V , V_{GS}=-4.5V , I_D=-6A	--	28	--	nC
Q_{gs}	Gate-Source Charge		--	7.7	--	
Q_{gd}	Gate-Drain Charge		--	7.5	--	
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=-15V , V_{GS}=-10V , R_G=3.3Ω, I_D=-6A	--	10	--	ns
t_r	Rise Time		--	35	--	
$t_{d(off)}$	Turn-Off Delay Time		--	110	--	
t_f	Fall Time		--	47	--	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	--	3500	--	pF
C_{oss}	Output Capacitance		--	323	--	
C_{rss}	Reverse Transfer Capacitance		--	222	--	

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Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=-25V , L=0.1mH , I_{AS}=-30A	81	--	--	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current [1,6]	V_G=V_D=0V, Force Current	--	--	-8.7	A
I_{SM}	Pulsed Source Current[2,6]		--	--	-18	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25°C	--	--	-1	V

Note:

1. Test data conducted with surface mount attachment to 1 inch^2, FR-4 board utilizing 2oz copper
2. Pulse Test. Pulse width ⍰ 300uS, duty cycle ≦ 2%
3. EAS data is a maximum rating. The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH
4. The power dissipation is limited by a 150°C maximum junction temperature
5. The Min. value is 100% EAS tested guarantee
6. The data is theoretically the same as I_D and I_{DM}. In real applications, it will be limited by total power

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Typical Characteristics

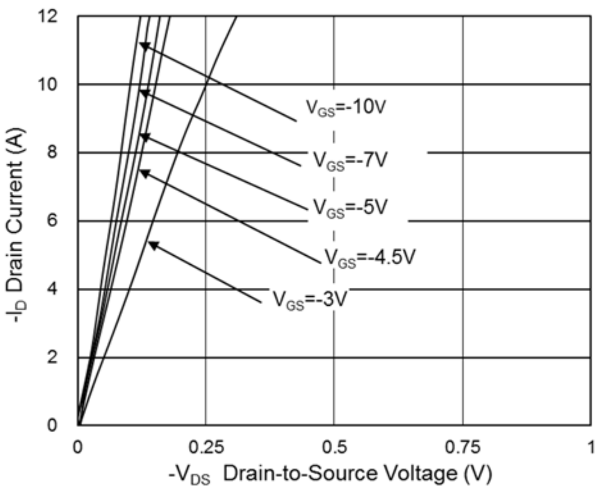

Fig.1: Typical Output Characteristics

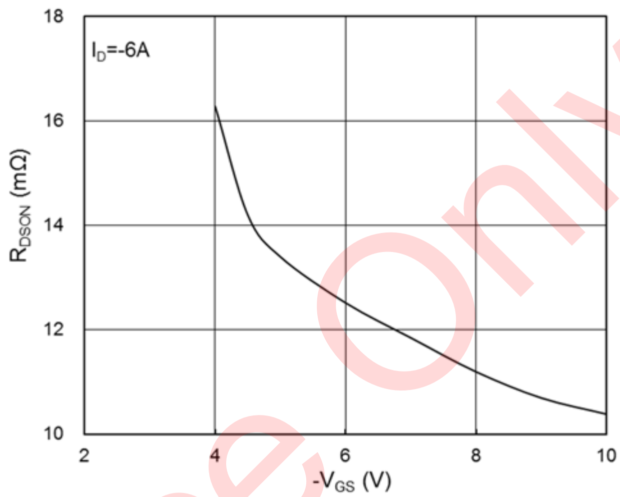

Fig.2: On-Resistance vs. Gate-Source

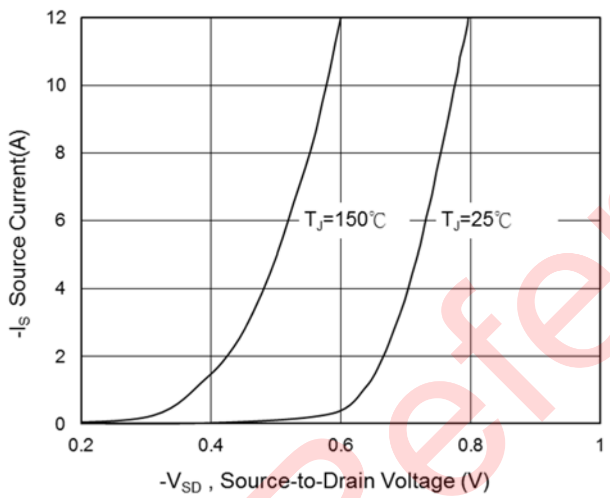

Fig.3: Forward Characteristics of Reverse

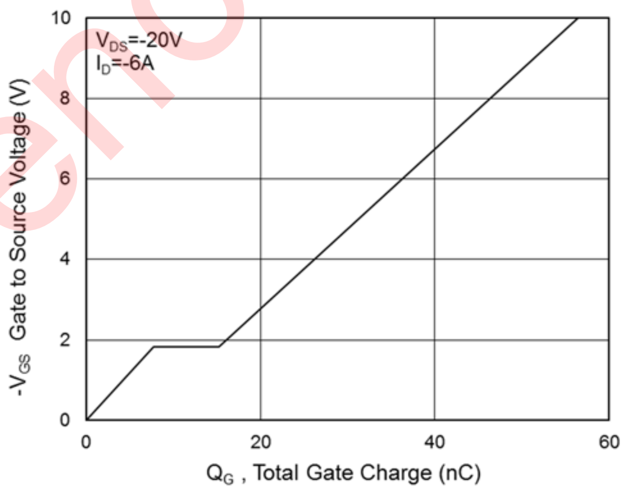

Fig.4: Gate-Charge Characteristics

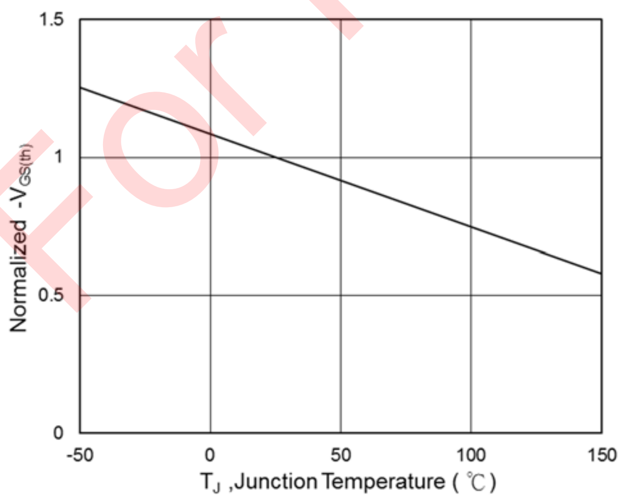

Fig.5: Normalized $V_{GS(th)}$ vs. T_J

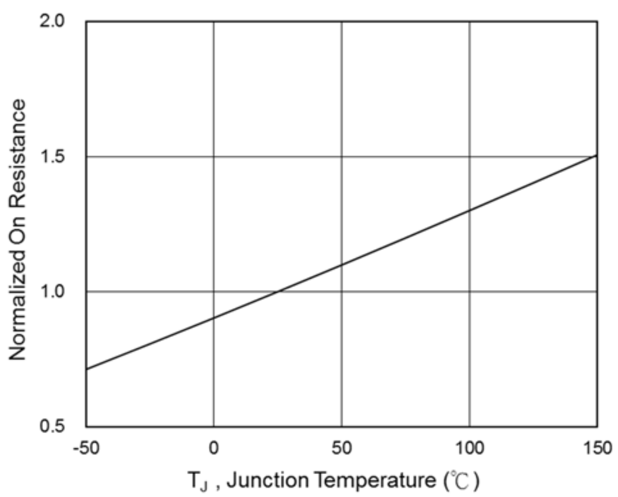

Fig.6: Normalized R_{DSON} vs. T_J

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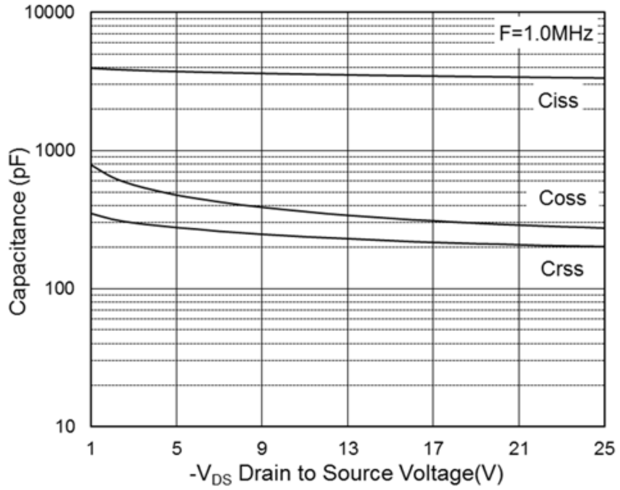

Fig.7: Capacitance

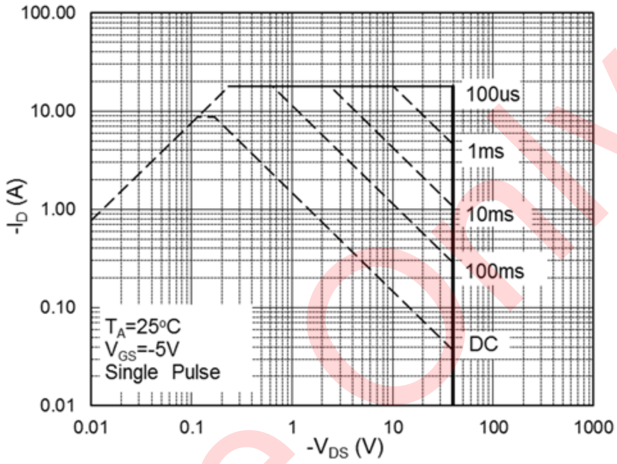

Fig.8: Safe Operating Area

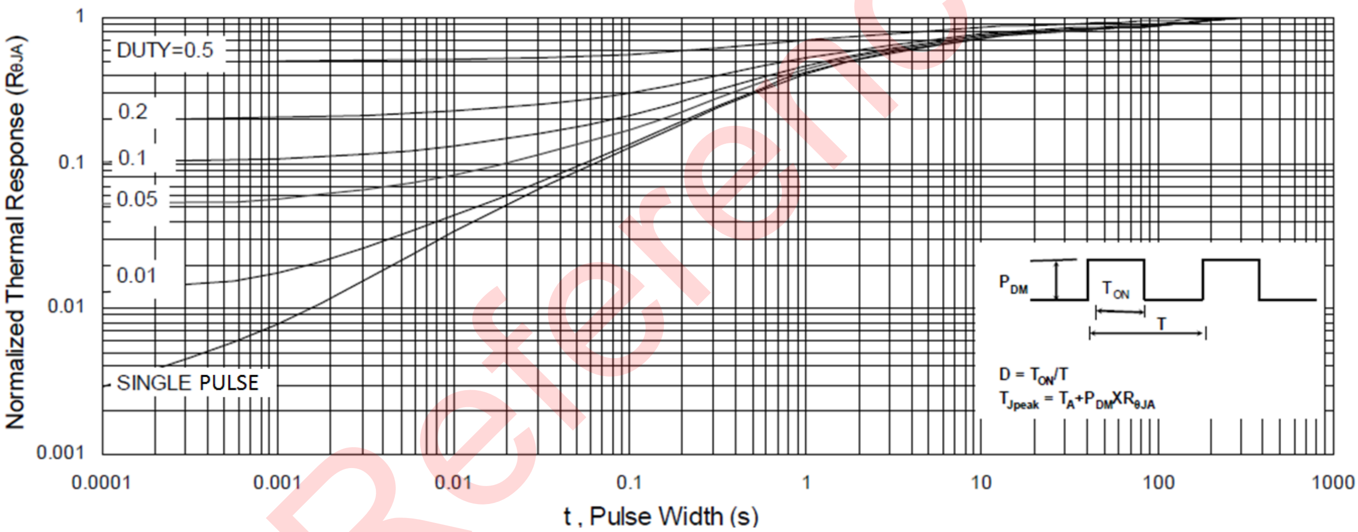

Fig.9: Normalized Maximum Transient Thermal Impedance

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